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## **Supporting Information**

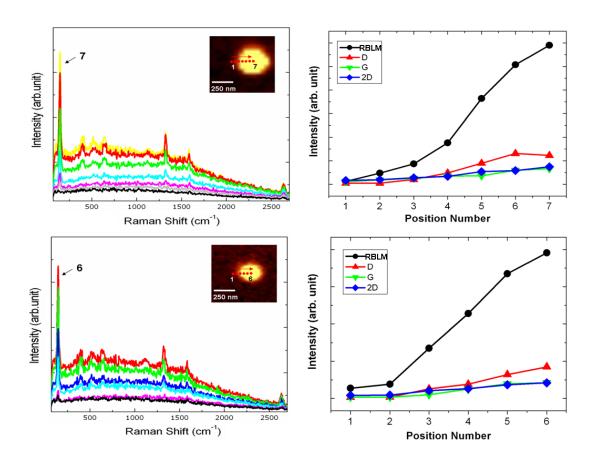
Investigation on Out-of-Plane Structural Properties of Graphene Monolayer with Gap-Plasmon :Mode-Selective Raman Enhancement and Influence of Additional SP<sup>3</sup> type Defect

Young Hwan Min and Won-Hwa Park\*

Material Characterization Team, Materials & Components R&D Lab, LG Electronics

Advanced Research Institute,

38, Baumoe-ro, Seocho-gu, Seoul, South Korea, 137-724



**Figure S1**. Two additional junctions showing similar lateral approach profiles and the resulting mode-dependent Raman enhancement.

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